

### Zener Diode Chips for ESD Protection

#### 1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge (ESD) protection application
- 1-2 This specification applies to N-Type silicon Zener diode chip Device NO:WT-Z106N-AU4

#### 2. Structure:

- 2-1 Planar type: N/P Diode
- 2-2 Electrodes:  
 Top side:Gold Pad.(Cathode)  
 Back side:Gold Layer.(Anode)

#### 3. Size:

- 3-1 Chip size: 6.88 mils x 6.88 mils (175  $\mu$ m x 175  $\mu$ m).
- 3-2 Chip thickness: 3.3  $\pm$  0.6 mils (85  $\mu$ m  $\pm$  15  $\mu$ m).
- 3-3 Active area: 4.1 mils x 4.1 mils (105  $\mu$ m x 105  $\mu$ m).
- 3-4 Bonding pad: 4.5 mils x 4.5mils (115  $\mu$ m x 115  $\mu$ m).
- 3-5 Pattern drawing: Refer to the attached drawing.

#### 4. Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	Vz	Iz=5mA	5.7	-	6.7	V
Reverse Leakage Current	IR	VR=4V	-	-	100	nA
Forward Voltage	Vf	If=20mA	-	-	1.2	V
Electrostatic Discharge	ESD	HBM MIL-STD883	8	-	-	KV

#### 5. Drawing:

